

13. (Amended) A method for fabricating a ferroelectric random access memory (FRAM) device comprising:

- b¹
- a) forming a lower electrode;
 - b) forming a lower seed layer on the lower electrode;
 - c) forming a ferroelectric layer on the lower seed layer;
 - d) forming an upper seed layer on the ferroelectric layer;
 - e) annealing the resultant structure of steps a) through d), including completing a perovskite crystal structure of the ferroelectric layer; and
 - f) forming an upper electrode on the upper seed layer.

b²

16. (Amended) The method according to claim 13, wherein forming the upper and lower seed layers includes using a ferroelectric material having a same lattice constant as that of a material for forming the ferroelectric layer.

b³

19. (Amended) The method according to claim 13, further comprising, prior to forming the lower electrode, forming a switching element to be electrically connected to the lower electrode.

20. (Amended) The method according to claim 13, further comprising:
before forming the lower electrode
providing a semiconductor substrate; and
forming a gate insulating layer on the semiconductor substrate, and